TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOS III)

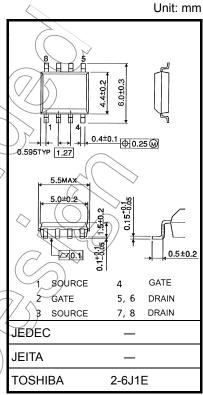
TPC8211

Lithium Ion Battery Applications
Portable Equipment Applications
Notebook PC Applications

- Low drain-source ON-resistance: RDS (ON) = 25 m Ω (typ.)
- High forward transfer admittance: $|Y_{fs}| = 7.0 \text{ S (typ.)}$
- Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$
- Enhancement mode: $V_{th} = 1.3 \text{ to } 2.5 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$

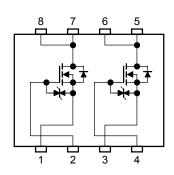
Absolute Maximum Ratings (Ta = 25°C)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	30	y
Drain-gate voltage (R_{GS} = 20 k Ω)			V_{DGR}	30	> V
Gate-source voltage			V _{GSS}	±20	V
Drain current	DC	(Note 1)	ΙD	5.5	^
Diain cunent	Pulse	(Note 1)	I _{DP}	22	
Drain power dissipation	Single-de operation		P _D (1)	1.5	*
(t = 10 s) (Note 2a)	Single-de at dual o	evice value peration (Note 3b)	(P _D (2))	1.1	
Drain power dissipation	Single-de operation		PD (1)	0.75	
(t = 10 s) (Note 2b)	Single-de at dual o	evice value peration (Note 3b)	P _{D (2)}	0.45	W
Single pulse avalanche energy (Note 4)		EAS	39.3	mJ	
Avalanche current			IAR	5.5	Α
Repetitive avalanche energy Single-device value at dual operation (Note 2a, 3b, 5)			EAR	0.1	mJ
Channel temperature			Toh	150	°C
Storage temperature range			I _{stg}	−55 to 150	°C



Weight: 0.085 g (typ.)

Circuit Configuration



Note: (Note 1), (Note 2), (Note 3), (Note 4) and (Note 5): See the next page.

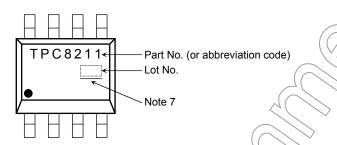
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Please handle with caution.

Thermal Characteristics

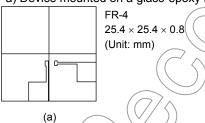
Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to ambient	Single-device operation (Note 3a)	R _{th (ch-a) (1)}	83.3	
(t = 10 s) (Note 2a)	Single-device value at dual operation (Note 3b)	R _{th} (ch-a) (2)	114	°C/W
Thermal resistance, channel to ambient	Single-device operation (Note 3a)	R _{th (ch-a) (1)}	167	
(t = 10 s) (Note 2b)	Single-device value at dual operation (Note 3b)	R _{th} (ch-a) (2)	278	

Marking (Note 6)

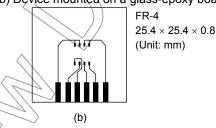


Note 1: Ensure that the channel temperature does not exceed 150°C

Note 2: a) Device mounted on a glass-epoxy board (a)



b) Device mounted on a glass-epoxy board (b)



Note 3: a)The power dissipation and thermal resistance values are shown for a single device.

(During single-device operation, power is only applied to one device.)

b) The power dissipation and thermal resistance values are shown for a single device.

b) The power dissipation and thermal resistance values are shown for a single device. (During dual operation, power is evenly applied to both devices.)

Note 4: $V_{DD} = 24 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 1.0 mH, $R_G = 25 \Omega$, $I_{AR} = 5.5 \text{ A}$

Note 5: Repetitive rating: pulse width limited by maximum channel temperature

Note 6: • on the lower left of the marking indicates Pin 1.



Note 7: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

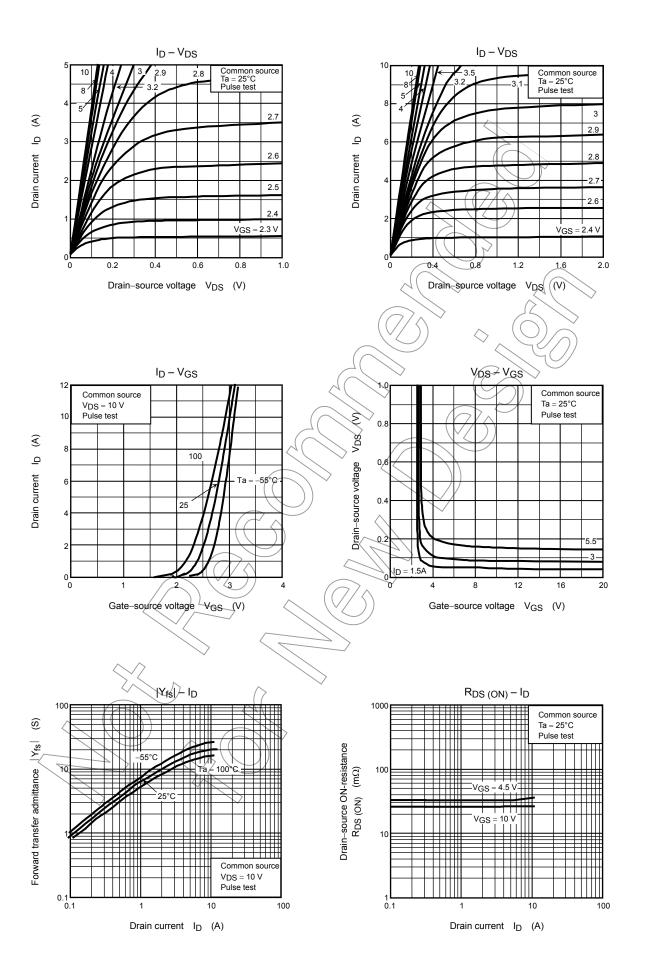
Electrical Characteristics (Ta = 25°C)

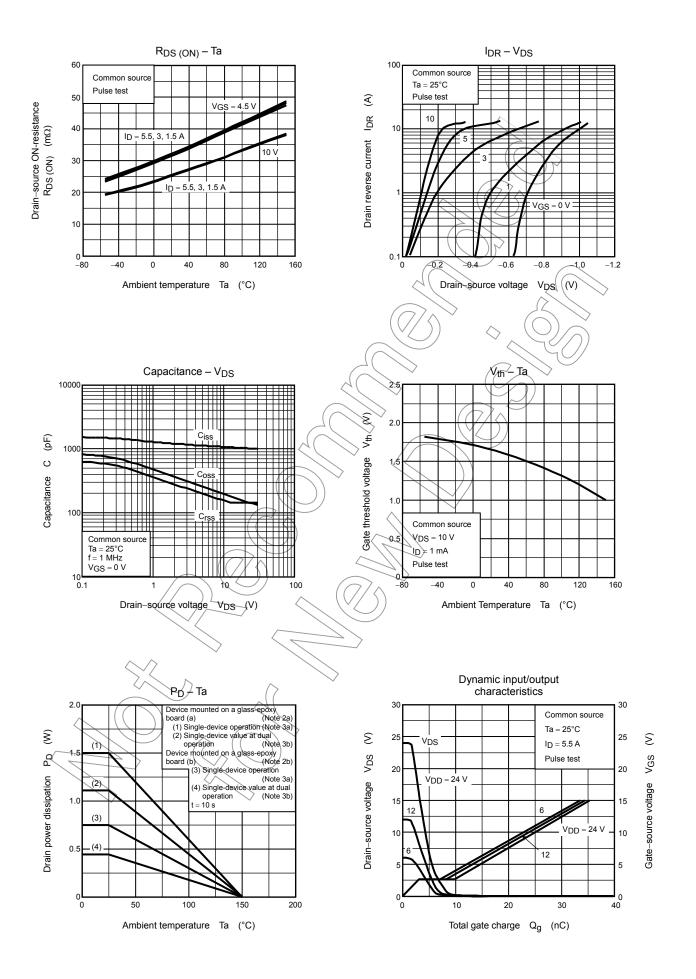
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	Gate leakage current		V _{GS} = ±16 V, V _{DS} = 0 V	_	_	±10	μΑ
Drain cut-OFF current		I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	_	_	10	μΑ
Drain-source breakdown voltage -		V _{(BR) DSS}	I _D = 10 mA, V _{GS} = 0 V	30	_	-	V
		V _{(BR) DSX}	I _D = 10 mA, V _{GS} = -20 V	15			V
Gate threshold voltage		V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.3) >-	2.5	V
Drain-source ON-resistance		R _{DS} (ON)	V _{GS} = 4.5 V, I _D = 3 A	\rightarrow	31	44	mΩ
		R _{DS} (ON)	V _{GS} = 10 V, I _D = 3 A)	25	36	
Forward transfer admittance		Y _{fs}	V _{DS} = 10 V, I _D = 3 A	3.5	7.0		S
Input capacitano	ce	C _{iss}		_	1250	_	
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	155	_	pF
Output capacitance		C _{oss}			170	\nearrow	
	Rise time	tr	10 V D	_ (5		
Switching time	Turn-ON time	t _{on}	V _{GS} 10 V) 1		ne
	Fall time	t _f			9	1	ns
	Turn-OFF time	t _{off}	Duty ≤ 1%, t _w = 10 μs) –	63	ı	
Total gate charge (Gate-source plus gate-drain)		Q _g (_	25	_	
Gate-source charge		Qgs	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5.5 \text{ A}$	_	20	_	nC
Gate-drain ("miller") charge		Qgd			5	1	

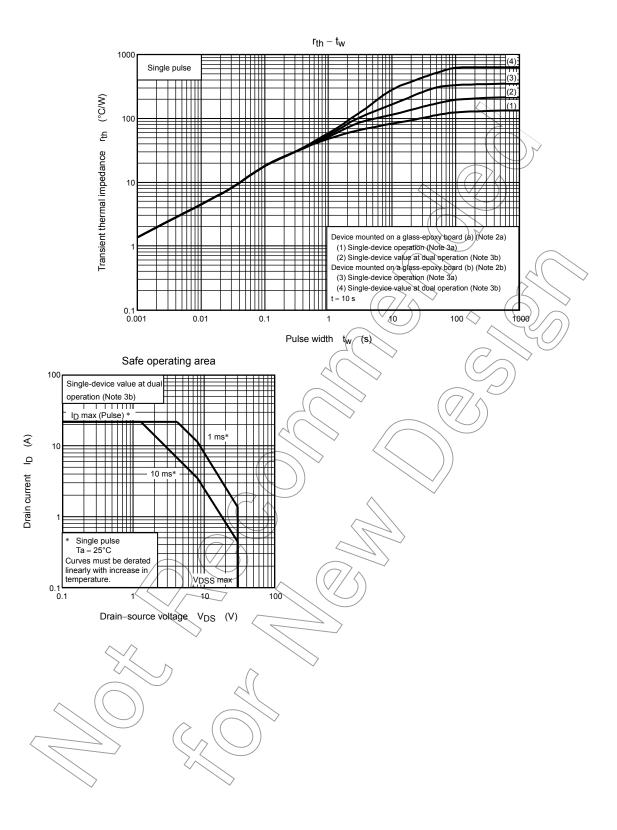
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characte	eristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)	\ \ I _{DRP} ⟨	_	_	_	22	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 5.5 A, V _{GS} = 0 V	-	-	-1.2	V

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